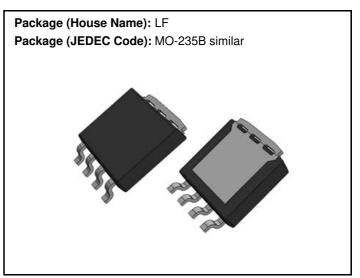
P40LF12SL

Power MOSFETs 120V, 40A, N-channel

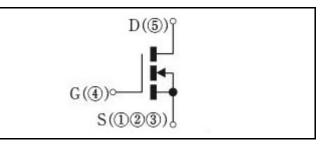
Feature

- N-channel
- Small SMD
- Large Current
- Low Ron
- 4.5V Gate Drive
- Low Capacitance
- Halogen free
- · Pb free terminal
- RoHS:Yes

OUTLINE



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C)

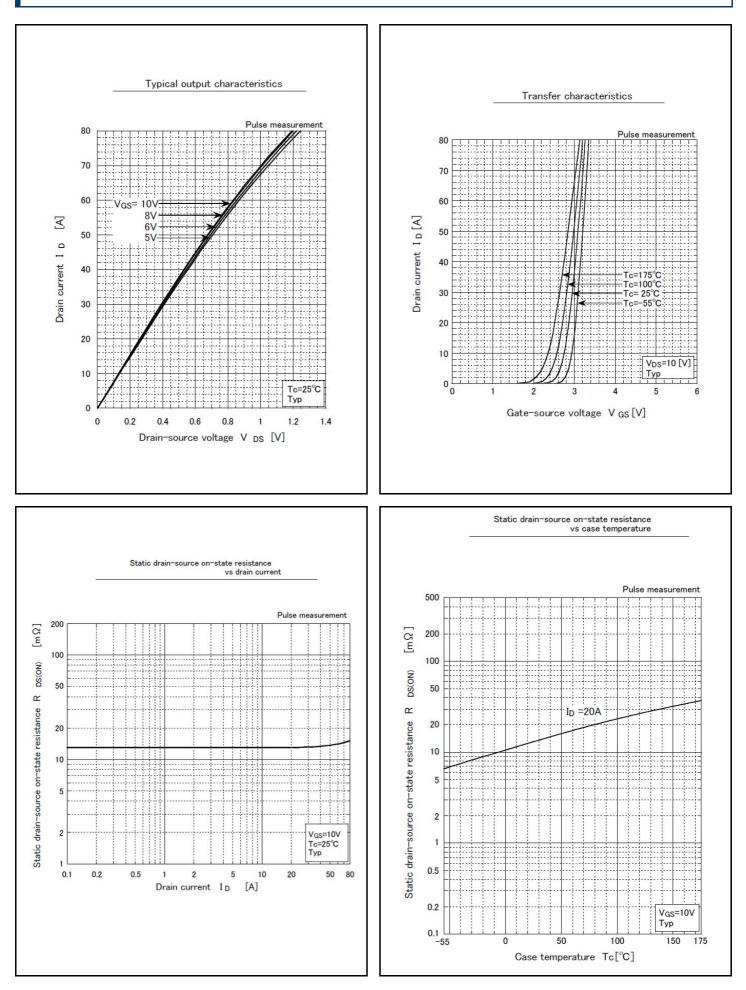
Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 175	°C
Channel tempertature	Tch		-55 to 175	°C
Drain-source voltage	V _{DSS}		120	V
Gate-source voltage	V _{GSS}		±20	V
Continuous drain current(DC)	I _D		40	A
Continuous drain current(Peak)	I _{DP}	Pulse width 10µs, duty=1/100	160	Α
Total power dissipation	P _T		217	W
Single avalanche current	I _{AS}	Starting Tch=25°C Tch≦150°C	30	A
Single avalanche energy	E _{AS}	Starting Tch=25°C Tch≦150°C	109	mJ

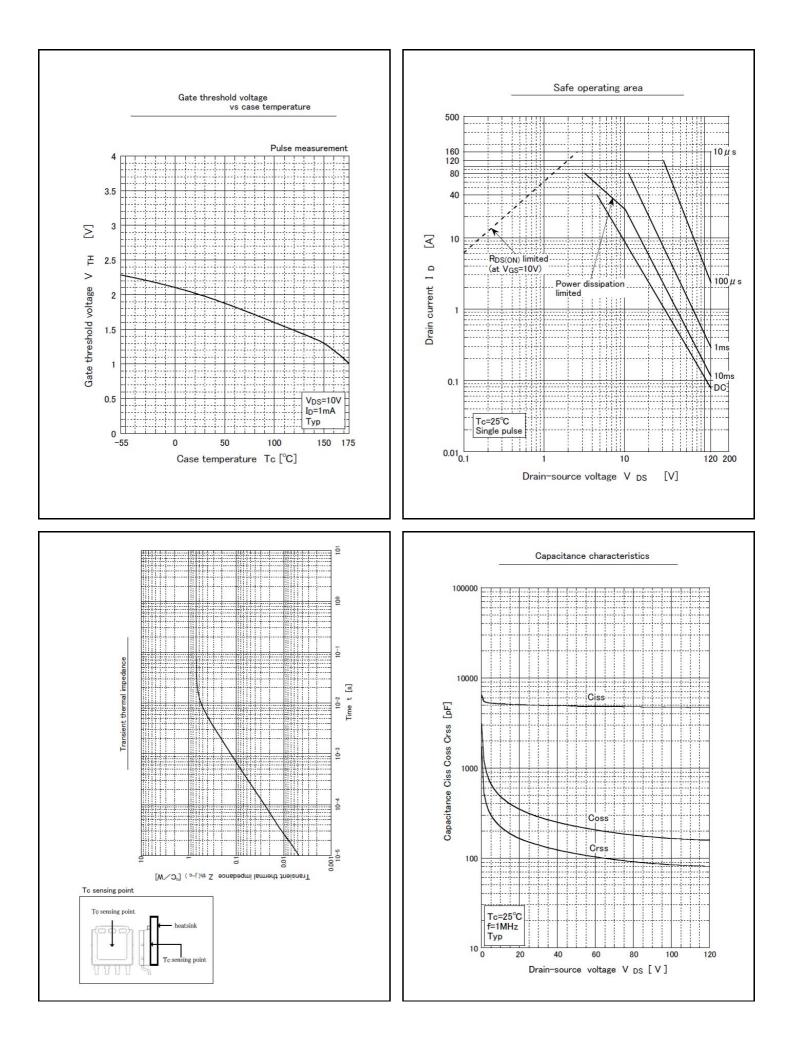
* : See the original Specifications

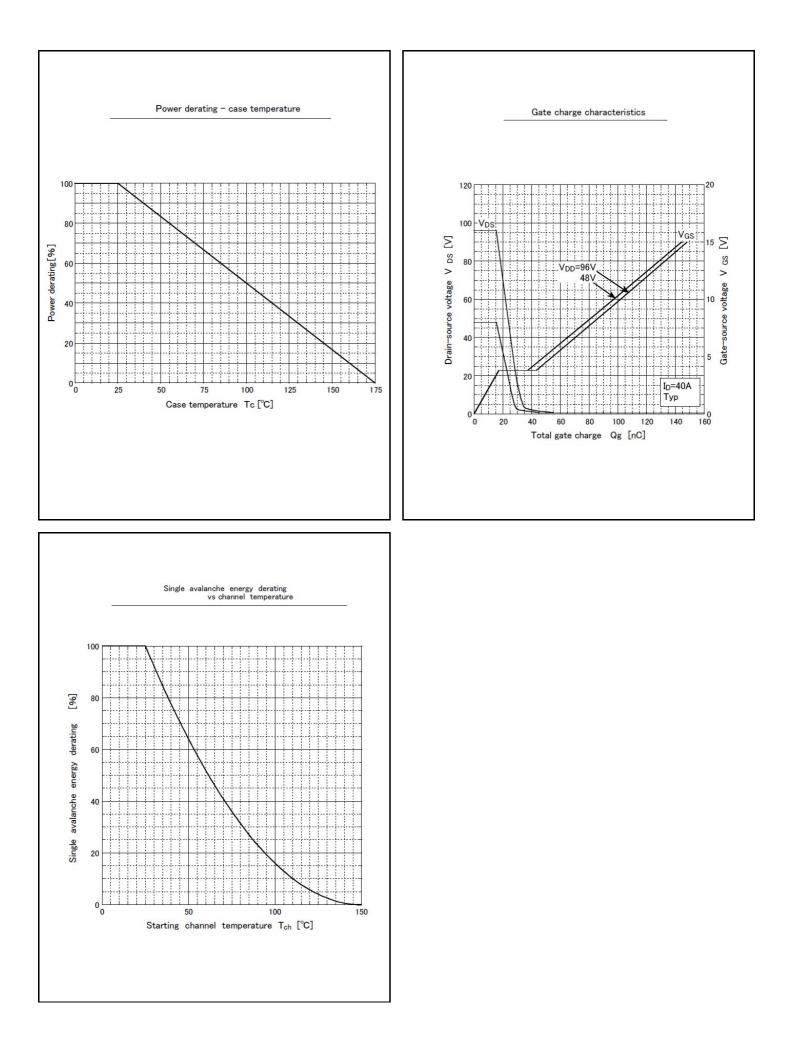
Item	Symbol	Conditions		Ratings		
			MIN	ТҮР	MAX	Unit
Drain-Source breakdown voltage	V _{(BR)DSS}	ID=1mA, VGS=0V	120			V
Zero gate voltage drain current	I _{DSS}	VDS=120V, VGS=0V			1	μA
Gate-source leakage current	I _{GSS}	VGS=±20V, VDS=0V			±0.1	μA
Forward transconductance	g fs	ID=20A, VDS=10V	20			S
Static drain-source on-state resistance	R _{DS(ON)}	ID=20A, VGS=10V		0.013	0.0163	Ω
Static drain-source on-state resistance	R _{DS(ON)}	ID=20A, VGS=4.5V		0.014	0.0187	Ω
Gate threshold voltage	Vth	ID=1mA, VDS=10V	1.5	2	2.5	V
Source-drain diode forward voltage	V_{SD}	IS=40A, VGS=0V			1.5	V
Thermal resistance	Rth(j-c)	Junction to case, with heatsink			0.69	°C/W
Total gate charge	Qg	VDD=96V, VGS=10V, ID=40A		102		nC
Gate to source charge	Qgs	VDD=96V, VGS=10V, ID=40A		17.5		nC
Gate to drain charge	Qgd	VDD=96V, VGS=10V, ID=40A		27		nC
Input capacitance	Ciss	VDS=25V, VGS=0V, f=1MHz		5000		pF
Reverce transfer capacitnce	Crss	VDS=25V, VGS=0V, f=1MHz		150		pF
Output capacitance	Coss	VDS=25V, VGS=0V, f=1MHz		312		pF
Turn-on delay time	td(on)	ID=20A, RL=3.00Ω, VDD=60V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		5.6		ns
Rise time	tr	ID=20A, RL=3.00Ω, VDD=60V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		8.5		ns
Turn-off delay time	td(off)	ID=20A, RL=3.00Ω, VDD=60V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		106		ns
Fall time	tf	ID=20A, RL=3.00Ω, VDD=60V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		33		ns
Diode reverse recovery time	trr	IF=40A, VGS=0V, di/dt=100A/µs		63		ns
Diode reverse recovery charge	Qrr	IF=40A, VGS=0V, di/dt=100A/µs		147		nC

* : See the original Specifications

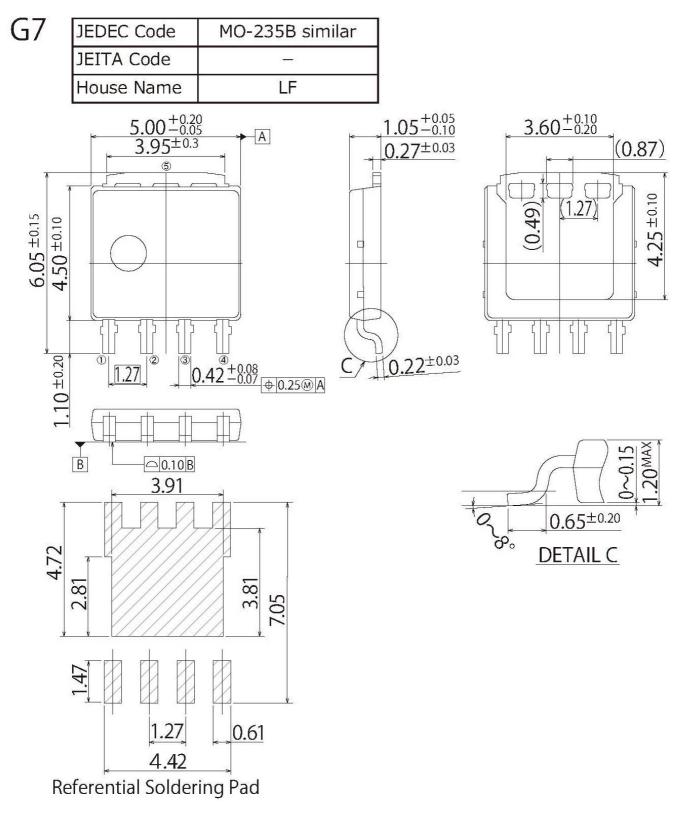
CHARACTERISTIC DIAGRAMS







unit:mm



Notes

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[Specific applications]

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